

Silicon PNP Power Transistors

2SA1021

DESCRIPTION

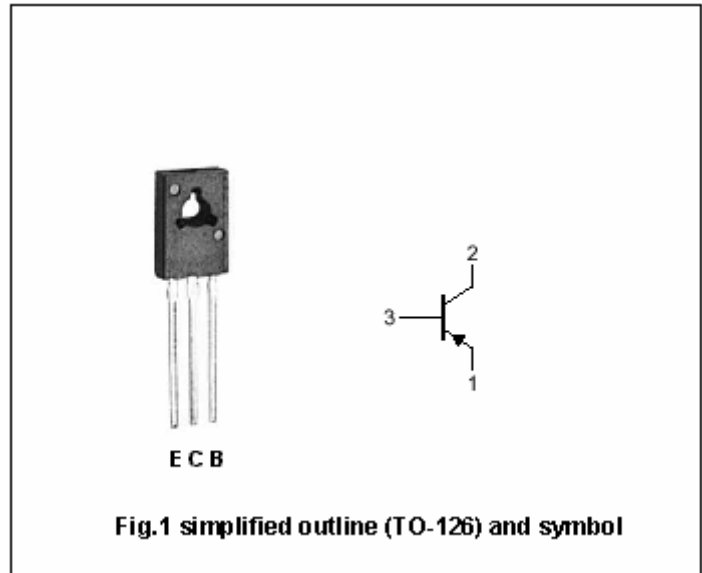
- With TO-126 package
- High breakdown voltage
- Large current capacity

APPLICATIONS

- For color TV sound output; converters
Inverters applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-1.5	A
I_{CM}	Collector current-Peak		-2.5	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.0	W
		$T_C=25^\circ\text{C}$	20	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-1mA; R _{BE} =∞		-150		V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-10 μ A; I _E =0		-150		V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10 μ A; I _C =0		-6		V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-500mA; I _B =-50mA			-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-1.0	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-1.0	μ A
h _{FE}	DC current gain	I _C =-150mA; V _{CE} =-5V	60		320	
f _T	Transition frequency	I _C =-50mA; V _{CE} =-10V	15			MHz

PACKAGE OUTLINE

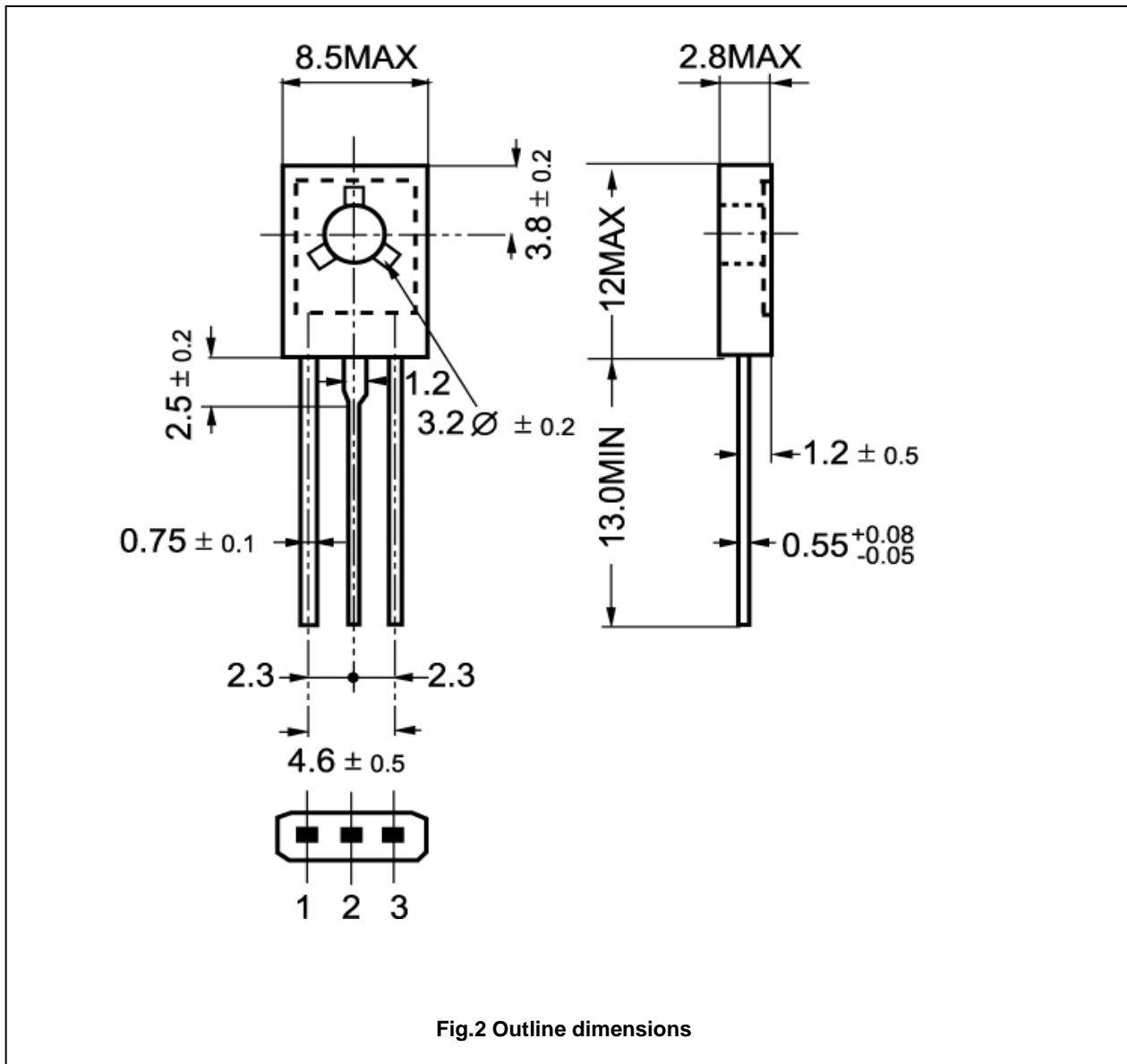


Fig.2 Outline dimensions